Valence instability of cerium under pressure in the K ondo-like perovskite

 $La_{0:1}Ce_{0:4}Sr_{0:5}M$ nO $_3$

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E ect of hydrostatic pressure and magnetic eld on electrical resistance of the K ondo-like perovskite manganese oxide, $La_{0:1}Ce_{0:4}Sr_{0:5}M$ nO₃ with a ferrim agnetic ground state, have been investigated up to 2.1 G Pa and 9 T. In this compound, the M n-m oments undergo double exchange mediated ferrom agnetic ordering at T_c 280 K and there is a resistance maximum, T_{m ax} at about 130 K which is correlated with an antiferrom agnetic ordering of cerium with respect to the M nsublattice m oments. Under pressure, the T_{m ax} shifts to lower tem perature at a rate of dT_{m ax}/dP = -162 K/G Pa and disappears at a critical pressure P_c 0.9 G Pa. Further, the coe cient, m of logT term due to K ondo scattering decreases linearly with increase of pressure showing an in ection point in the vicinity of P_c. These results suggest that cerium undergoes a transition from Ce³⁺ state to C e⁴⁺ /C e³⁺ m ixed valence state under pressure. In contrast to pressure e ect, the applied m agnetic eld shifts T_{m ax} to higher tem perature presum ably due to enhanced ferrom agnetic M n m oments.

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Perovskite manganites $R_{1 x} A_{x} M nO_{3}$ (R = trivalent rare earth: A = divalent alkaline earth) have been investigated extensively due to a lot of fascinating electronic properties such as insulator-m etal transition (I-M), colossalm agnetoresistance (CMR) and charge, orbitaland spin ordering. Magnetic eld, pressure, photons and electric eld are the external param eters by which the size, existence and interplay of these e ects can be varied.^{1,2} It is well known that the ground state properties of half-doped m anganites, R 0:5A 0:5M nO 3 depend upon the width (W) of one electron conduction band; W is controlled by the average size (r_A) of the di erent A -cations through M n-O -M n bond angle. For exam ple, $La_{0:5}Sr_{0:5}M nO_3$ with larger W ($r_A = 1.263 A$) is a m etallic ferrom agnet in the ground state.³ This behavior has been explained by a theoretical scenario based on the double exchange (DE) interaction between M n^{3+} and M n⁴⁺ ions, where the spins of e_{α} electrons or holes are aligned in the direction of the t_{2g} local spins by H und coupling and electrical conduction arises due to the hopping of the charge carriers from one ion to the next without changing their spin orientation.4,5,6

In compounds containing rare earth elements, cerium is well known to exhibit a wide variety of electronic properties such as valence change, heavy fermion, superconductivity and magnetic ordering. In Pr_{0:1}C e_{0:4}Sr_{0:5}M nO₃ compound having largerW, K ondo

like behavior and anom alous magnetic ordering of Ce were reported.⁷ In this system, there is a structural phase transition at 250 K from the high temperature orthorhom bic phase (space group: Im m a) to the low tem perature tetragonalphase (I4=m cm) which is accom panied by a ferrom agnetic ordering of m anganese m oments due to DE interactions, and Cemoments order antiferrom agnetically with respect to M n m om ents below Т 120 K. The electrical resistivity increases anom alously with decrease of tem perature, particularly below the Curie tem perature T_C, exhibiting a resistivity maximum at 120 K (T_{max}) , which corresponds to the ordering of Cemoments, and a minimum at 15 K ($T_{m in}$). The anom alous tem perature dependence of resistivity R (T) is in contrast to the expected metallic behavior below T_C due to D E interactions. Sim ilar results were reported for La0:1Ce0:4Sr0:5M nO 3 with the ferrom agnetic ordering of M n-m om ents at T_C 280 K and Ce ordering be-130 K.⁸ In these systems with larger W , since low there is no charge ordering of manganese ions and the M n-sublattice rem ains ferrom agnetic down to 1.8 K, the resistivity anomaly has been attributed to Kondo-like scattering of M n \mathbf{e}_{α} conduction electrons by the localized Ce:4f m om ents. The decrease of resistivity below T_{m ax} or cerium ordering tem perature is due to reduced spin dependent scattering.

In order to get more insight into the nature of in-

teractions between the localized Ce:4f and ferrom agnetic M n m om ents, we have investigated a simultaneous and individual e ects of hydrostatic pressure and m agnetic eld on the behavior of electrical resistance in La_{0:1}Ce_{0:4}Sr_{0:5}M nO₃ within a tem perature range of 4.2 K { 300 K. We use this approach because our earlier am bient-pressure work clearly established that the resistivity features are correlated with m agnetization and neutron di raction data.^{7,8} From this study, we substantiate that the anom alous tem perature dependence of electrical resistance is due to K ondo-like scattering of M n e_g electrons by localized C e:4f m om ents. Further, we infer that there is a valence change of cerium under pressure from Ce³⁺ state to Ce⁴⁺/Ce³⁺ m ixed valence state.

Polycrystalline sample of $La_{0:1}Ce_{0:4}Sr_{0:5}MnO_3$ was prepared by calcining stoichiom etric mixtures of La_2O_3 , CeO_2 , $SrCO_3$, Mn_2O_3 at 1100 C and sintering at 1500 C. Phase purity, nuclear and magnetic structures were determined by powder x-ray and neutron di raction methods.⁸ The electrical resistance was measured by a standard four-probe method with a direct current of 1 m A down to 4.2 K. The electrical contact was made with a silver paint of heat treatment type. Hydrostatic pressure up to 2.1 GPa was generated by using a Cu-Be piston-cylinder device and 1:1 mixture of Fluorinert FC 70 and FC 77 as a pressure medium. The pressure was changed at RT to minimize internal strain in the specimen and the load was controlled to within 1% through-

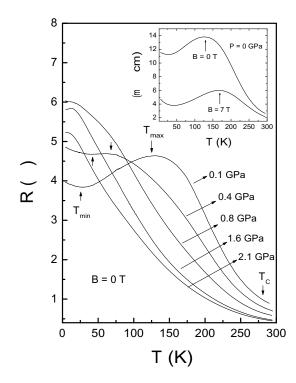


FIG.1: Tem perature dependence of the electrical resistance R (T) of $La_{0:1}Ce_{0:4}Sr_{0:5}M$ nO₃ at high pressures. The downward and upward arrows indicate $T_{m ax}$ and $T_{m in}$, respectively. T_{C} is nearly 280 K. Inset shows the shift of $T_{m ax}$ to a higher tem perature under a magnetic eld of 7 T and P = 0G Pa.

out the m easurem ent. The m agnetic eld was applied by a superconducting m agnet up to 9 T. The details of the present apparatus at multi-extrem e conditions have been reported previously.¹⁰

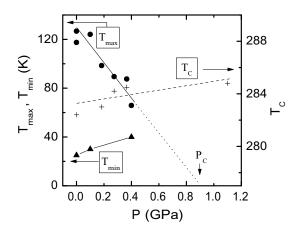


FIG.2: Pressure dependence of $T_{m \ ax}$ and $T_{m \ in}$ at B = 0 T as shown by solid circle and triangle, respectively. The solid, dashed and dotted lines are guides for the eye. P_c is the value of pressure corresponds to the extrapolation of $T_{m \ ax}$ to zero tem perature.

Tem perature dependence of electrical resistance at various pressures is shown in Fig. 1. In this gure, there is no indication for the DE ferrom agnetic m etallic transition near T_C 280 K. However, we have already reported⁹ from the tem perature derivative of R that, in this system, the T_{C} increases with pressure at a rate of $dT_{\rm C}/dP = + 1.9 \, \text{K}/\text{GPa}$, as shown in Fig.2. The small increase of T_C is consistent with the fact that this system is in a weak coupling region due to a large lling of conduction band, where the system is less sensitive to pressure or change in W.¹⁵ At 0.1 GPa, R increases logarithm ically (log T) with decreasing tem perature in the 180 { 230 K as shown by solid line in Fig. 3(a) range and exhibits a broad maximum at about 130 K (T_{max}) and a m in im um at about 30 K ($T_{m in}$) which are shown by arrows in Fig1. As discussed earlier, 7 the $\rm T_{m\ ax}$ is due to the onset of antiferrom agnetic ordering of Ce^{3+} m om ents with respect to the ferrom agnetic M n m om ents. This R (T) behavior is rem in iscent of the typical concentrated K ondo com pounds.^{12,13} H owever, the origin of T_{max} in the present case should be com pared and contrasted with the concentrated K ondo system swhere the origin of resistivity maximum is due to crystal eld e ects and K ondo coherence, and the $T_{m\ ax}$ has a large positive pressure coe cient.13,14 Further, the decrease of resistivity below Ce ordering is not sharp such as one norm ally observes at a magnetic ordering of Ce in interm etallics. This is because, the antiferrom agnetic coupling in the present system is between Ce and Mnm om ents and the antiparallel arrangement of Ce is induced by Mn moments.⁸ In fact, a recent theoretical analysis on this system reproduce the magnetic behavior of M n and Ce in this system .¹⁶

In the present case, with increasing pressure, $T_{m \ ax}$

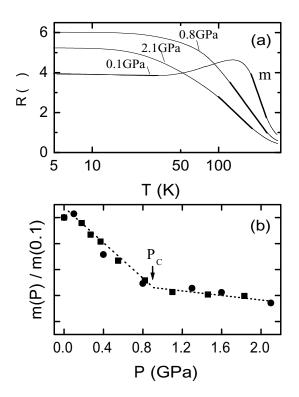


FIG. 3: (a) Temperature dependence of R, in which the abscissa is selected as a logarithm ic scale and log T dependence is shown by solid lines. (b) P ressure dependence of the normalized coe cient m (P)/m (0.1) of log T term. The previous data of m (P)/m (0.1)⁹ is described as closed circle. P_c is de ned as an in ection point of the coe cient. The dotted and solid lines are guides for the eye.

shifts to a lower tem perature at a rate of $dT_{m ax}/dP =$ -162 K /GPa, which is in sharp contrast to the typical concentrated K ondo system s, for example, C eA & or $C \, \text{eInC} \, u_2$ where the $T_{\text{m ax}}$ increases with pressure. 12,13 O n the other hand, $T_{\text{m in}}$ seem s to shift to higher tem perature as shown in Fig. 2. At pressures higher than 0.8 GPa both $T_{m\mbox{ ax}}$ and $T_{m\mbox{ in}}$ are not seen down to $4.2\mbox{ K}$. It should be noticed from the Fig. 2 that the extrapolated value of pressure, where the T_{max} equals to zero, is 0.9 GPa, which we term ed as critical pressure P_c . Since the T_m ax corresponds to the ordering tem perature of cerium, the P_c m ight indicate the suppression of magnetic ordering of cerium. A coording to the e ect of hydrostatic pressure on DE ferrom agnetism r^{15} we would expect that the T_{max} associated with Ce ordering should increase with pressure. The observed decrease of $T_{m\ ax}$ or the magnetic ordering temperature of cerium with increase of pressure rather indicates a valence change of cerium from Ce^{3+} towards Ce^{4+} state. In contrast to pressure e ect, the application of magnetic eld (B) shifts the T_{max} to higher temperature due to enhanced ferrom agnetic M n m om ents, as shown in the inset of Fig.1, for an applied eld of 7 T. The presence of resistivity m in im um in the vicinity of 25 K in manganites is well known and has been attributed to the e ect of electron-electron interactions.¹⁷

It is intriguing and important to note the change of R (T) at various pressures as a function of temperature (see Fig. 1). Near $T_{\rm C}$, the decrease of R with increase ofpressure is due to; (i) widening of eq band as reported for $La_{1 x} Sr_{x} M nO_{3}^{15}$ and (ii) valence change of cerium ion. On the other hand, at the lowest tem perature measured (4.2 K), R increases with pressure up to 0.8 GPa, close to P_c, and then decreases with further increase of pressure. Since the pressure e ect on the DE ferrom aqnet with larger W does not have any contribution to R at low tem peratures, the increase of R suggests that the strength of J, the exchange integral, which depends on the hybridization between the conduction electron and f-electron, increases with pressure. The decrease of R above $P_{\,\mathrm{c}}$ m ay be due to decrease of $T_{\,\mathrm{m}\mbox{ ax}}$. In the inter-250) the large decrease of R mediate region (90 Т with increase of pressure is mainly due to suppression of spin dependent scattering that results from the valence change of ærium. The fact that the R (T) does not becom e a m etallic like even at 2.1 GPa suggests that the cerium has not completely changed to Ce⁴⁺ state and rather exists in Ce^{4+}/Ce^{3+} m ixed valence state. Fig.3a, shows variation of R at various pressures as a function of tem perature in logarithm ic scale. It can be seen that there is a region of logT dependence of R at high tem peratures (> 100 K) as shown by solid line at all pressures. This is a signature of K ondo scattering of conduction electrons by the localized m om ents. The coe cients of logT term is term ed as m. In Fig.3b, norm alized coe cientm (P)/m (0.1) is plotted as a function of pressure, where m (P) is de ned as m = 0 (R = 0 log T, and m (0.1) is that at 0.1 GPa. The coe cient, m (P)/m (0.1) decreases linearly with increase of pressure because of the change in valence state of cerium as discussed above. This behavior is also di erent qualitatively from that of the typical Kondo com pounds.¹⁴ Near P_c 0.9 G Pa, a small in ec-

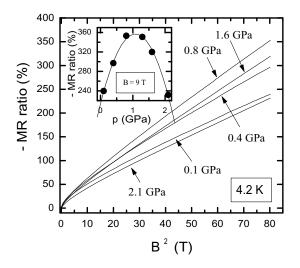


FIG. 4: Pressure dependence of negative MR ratio (= R = R (B) 100 %) at 42 K. The MR ratio at 9 T is plotted in the inset as a function of pressure. A solid curve is guide for the eye.

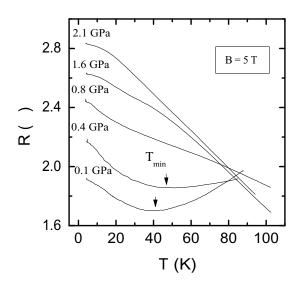


FIG.5: Pressure dependence of R(T) at magnetic eld of 5T. It can be seen that R at 4.2 K increases monotonically with pressure contrary to zero applied eld (see Fig. 1).

tion is seen and above which the e ect of pressure on m becomes smaller, indicating a decrease in the strength of the K ondo scattering above P_c . This is consistent with the observation that the $T_{m \ ax}$ disappears at P_c , where one would expect a change in the interaction between the Ce:4f local and the conduction electron m om ents.

M agnetoresistance (M R) ratio (R=R(B)=(R(0)-R(B))/R(B)) at various pressures at 4.2 K is plotted as a function of B^2 in Fig. 4. The negative CM R e ect in perovskitem anganese oxides is well known as reported in previous experim ents². In the present experim ent, the negative M R m onotonically increases with applying B which is mainly due to suppression of K ondo-like scattering and a sm all contribution from grain boundary scattering, as the DE interactions in large W m aterials results in M R e ect only near T_c .⁷ Above 5 T, M R lineary increases with respect to B², revealing the existence of spin-dependent scattering. The inset show s M R ratio at 4.2 K and at a eld of 9 T as a function of pressure: M R increases with pressure and a peak is clearly seen near P_c

0.9 GPa. This is consistent with the observation that the pressure dependence of R at 4.2 K has sim ilar behavior, indicating the electronic changes associated with the valence change of cerium .

The pressure dependence of R (T) (T < 100 K) under a magnetic eld of B = 5 T is shown in Fig.5. By applying 5 T, T_m in shifts from 30 K to 40 K at 0.1 GPa. This phenom enon was explained by the enhancement of cerium ordering induced by the ferror agnetic manganese moments⁷. In contrast to zero applied eld, R at 4.2 K and 5 T increases with increasing pressure without showing any maximum in the present pressure range. It is possible that P_c exceeds the maximum pressure limit in our experiment because the ordering temperature of cerium increases with applied magnetic eld? T_m in creases with pressure similar to that observed under zero

eld as shown Fig. 2. It would be interesting to carry out neutron di raction experim ent under pressure to see the changes in the ordering tem perature of cerium.

In conclusion, we have found that under zero applied magnetic eld, the $T_{m\ ax}$ due to magnetic ordering of cerium and normalized coe cient of logT term, m (P)/m (0.1) originated from K ondo-like scattering of conduction electrons decrease with increasing pressure. Further, the $T_{m\ ax}$ disappear at a critical pressure (P_c 0.9 GPa) where there is a corresponding change in the slope of the coe cient of the logT term, indicating a decrease in the strength of the K ondo-like scattering. The suppression of $T_{m\ ax}$ has been attributed to a valence change of cerium from $C\ e^{3+}$ state to $C\ e^{4+}/C\ e^{3+}$ m ixed valence state under pressure.

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